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(57) **ABSTRACT**

Techniques are provided herein to form semiconductor devices that include an elongated contact having two different heights on a source or drain region. A semiconductor device includes a gate structure around or otherwise on a semiconductor region (or channel region) that extends from a source or drain region. An elongated conductive contact is formed over the source or drain region that stretches or otherwise extends laterally across the source/drain trench above an adjacent source or drain region without contacting the adjacent source or drain region. A conductive via may contact the portion of the conductive contact over the adjacent source or drain region. Accordingly, the conductive contact may have a first thickness above the source or drain region and a second thickness above the adjacent source or drain region with the first thickness being greater than the second thickness.

